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NTE2365

Silicon NPN Transistor

High Voltage Horizontal Deflection Output

TO3PBL Type Package

Features:

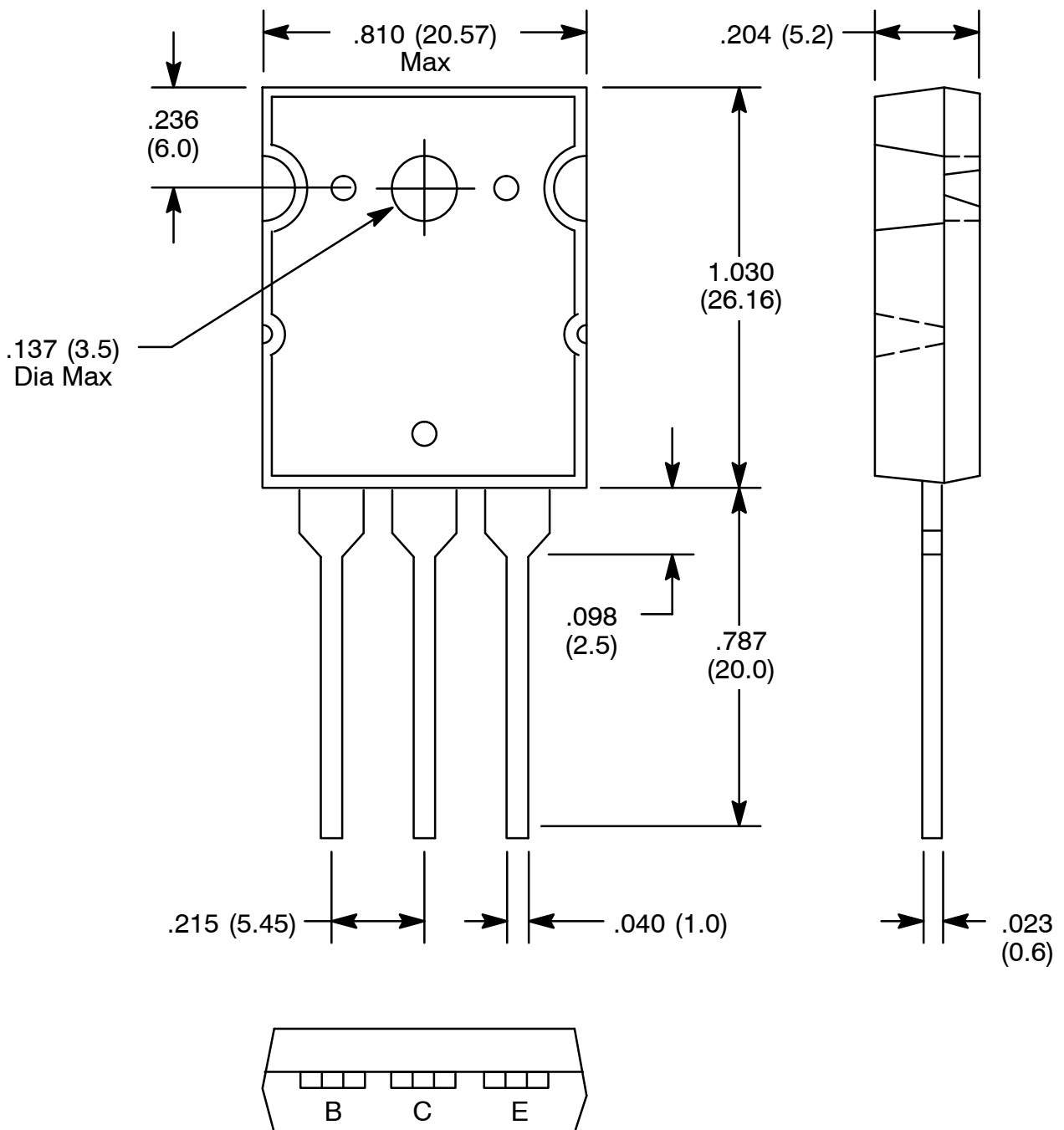
- High Speed: $t_f = 100\text{ns typ}$
- High Reliability
- High Breakdown Voltage: $V_{CBO} = 1500\text{V}$

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector to Base Voltage, V_{CBO}	1500V
Collector to Emitter Voltage, V_{CEO}	800V
Emitter to Base Voltage, V_{EBO}	6V
Collector Current, I_C	
Continuous	15A
Peak	35A
Collector Dissipation, P_C	180W
Junction Temperature, T_J	$+150^\circ\text{C}$
Storage Temperature Range, T_{stg}	-55° to $+150^\circ\text{C}$

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 800\text{V}, I_E = 0$	–	–	10	μA
	I_{CES}	$V_{CE} = 1500\text{V}, R_{BE} = 0$	–	–	1.0	mA
Collector Sustaining Voltage	$V_{CEO(sus)}$	$I_C = 100\text{mA}, I_B = 0$	800	–	–	V
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 4\text{V}, I_C = 0$	–	–	1.0	mA
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10\text{A}, I_B = 2.5\text{A}$	–	–	5	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 10\text{A}, I_B = 2.5\text{A}$	–	–	1.5	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = 5\text{V}, I_C = 1\text{A}$	8	–	30	
	$h_{FE(2)}$	$V_{CE} = 5\text{V}, I_C = 10\text{A}$	4	–	8	
Storage Time	t_{stg}	$I_C = 8\text{A}, I_{B1} = 1.6\text{A}, I_{B2} = -3.2\text{A}$	–	–	3.0	μs
Fall Time	t_f		–	–	0.2	μs



Note: Pin2 connected to metal part of mounting surface.